

Substitute for form 1449A/B/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>			Application Number	10/634,897-Conf. #7348	
			Filing Date	August 6, 2003	
			First Named Inventor	Terry L. Gilton	
			Art Unit	2813	
			Examiner Name	Not Yet Assigned NGUYEN	
Sheet	1	of	1	Attorney Docket Number	M4065.0700/P700-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
TN	BA	GB 1131740A	10/23/1968	Tolutis		

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NON PATENT LITERATURE DOCUMENTS			
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TN	CA	Y. KAWAMOTO, "Ionic Conduction in As ₂ S ₃ -Ag ₂ S, GeS ₂ -GeS-Ag ₂ S and P ₂ S ₅ -Ag ₂ S Glasses," J. Non-Crystalline Solids, 20 (1976) 393-404.	

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T. NGUYEN 5/26/04

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Substitute for form 1449A/PTO <h1>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h1> <p><i>(use as many sheets as necessary)</i></p>				Complete if Known Application Number: NOT YET ASSIGNED 10/634897 Filing Date: August 6, 2003 First Named Inventor: Terry L. Gilton Art Unit: NOT YET ASSIGNED 2813 Examiner Name: NOT YET ASSIGNED Nguyen Attorney Docket Number: M4065.0700/P700-A	
Sheet	1	of	1		

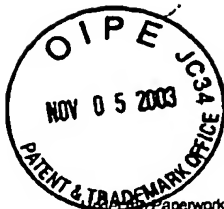
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Examiner Signature	T. NUYEN	Date Considered	5/26/04
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			Examiner Name	Not Yet Assigned Tuan Nguyen	
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		Number-Kind Code ² (if known)				
TN	AA	US-6,117,720		09/12/2000	Harshfield	
	AB	US-3,450,967		06/17/1969	Tolutis	
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				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2813
				Examiner Name	Not Yet Assigned
Sheet	2	of	11	Attorney Docket Number	M4065.0700/P700-A

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*	q	US-2003/0001229 APP	1/2/2003	Moore et al.	
*	r	US-2002/0127886 APP	9/12/2002	Moore et al.	
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*	u	US-6,072,716	6/2000	Jacobson et al.	
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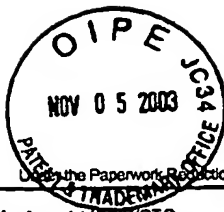
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Sheet	3	of	11	Attorney Docket Number	M4065.0700/P700-A

* <i>TN</i>	A29	US-5,512,328	04/1996	Yoshimura et al.	
* <i>TN</i>	A30	US-6,117,720	09/2000	Harshfield	

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<i>TN</i>	BA	WO 97/48032	12/18/1997	Kozicki et al.		
* <i>TN</i>	BB	WO 99/28914	06/10/1999	Kozicki et al.		
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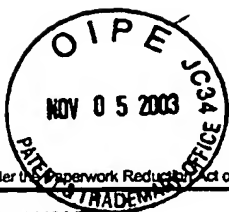


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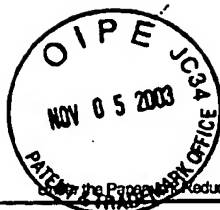


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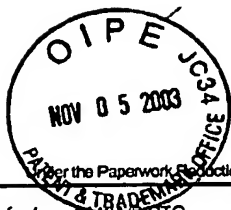
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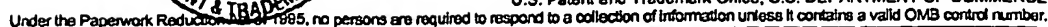


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